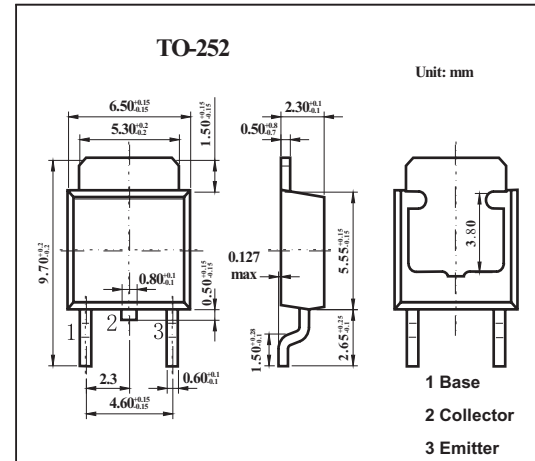


Silicon PNP Epitaxial Planar Type

2SB928A

■ Features

- High collector to emitter V_{CE0}
- High collector power dissipation P_c

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-200	V
Collector-emitter voltage	V_{CE0}	-180	V
Emitter-base voltage	V_{EB0}	-6	V
Peak collector current	I_{CP}	-3	A
Collector current	I_C	-2	A
Collector power dissipation	P_c	30	W
		1.3	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

* Single pulse, $P_w=10\text{ms}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -200\text{V}, I_E = 0$			-50	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-50	μA
Collector to base voltage	V_{CB0}	$I_C = -500\mu\text{A}, I_E = 0$	-200			V
Collector to emitter voltage	V_{CE0}	$I_C = -5\text{mA}, I_B = 0$	-180			V
Emitter to base voltage	V_{EB0}	$I_E = -500\mu\text{A}, I_C = 0$	-6			V
Forward current transfer ratio	h_{FE}	$V_{CE} = -10\text{V}, I_C = -150\text{mA}$	60		240	
		$V_{CE} = -10\text{V}, I_C = -400\text{mA}$	50			
Base to emitter voltage	V_{BE}	$V_{CE} = -10\text{V}, I_C = -400\text{mA}$			-1	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}, f = 10\text{MHz}$		30		MHz

■ h_{FE} Classification

Rank	Q	P
h_{FE}	60 to 140	100 to 240